## Abstract Submitted for the 4CS20 Meeting of The American Physical Society

Validating Surface Energy Measured by Three Liquid Contact Angle Analysis with Computed Gibbs Energy for  $\text{LiNbO}_3/\alpha$ -Quartz SiO<sub>2</sub> for Direct Wafer Bonding ABBIE ELISON, MOHAMMED SAHAL, SHEFALI PRAKASH, SRIVATSAN SWAMINATHAN, RILEY RANE, BRIAN BAKER, JA-COB KINTZ, ALIYA YANO, SAAKETH NARAYAN, ALEX BRIMHALL, LAU-REN PUGLISI, DR. ROBERT CULBERTSON, DR. NICOLE HERBOTS, Arizona State University, Dept. of Physics, PROF HERBOTS' NANO-BONDING RESEARCH TEAM — LiNbO<sub>3</sub> is a ferro-electric with the most significant electrooptical, piezo-electric properties, and a near perfect linear response. Hence, LiNbO<sub>3</sub> is an ideal material to integrate piezoelectrics monolithically to Si. But lattice and thermal expansion mismatches between  $LiNbO_3$  and  $Si/SiO_2$  are incompatible with hetero-epitaxy and Direct Wafer Bonding (DWB). This work investigates DWB at RT via Nano-Bonding<sup>TM, 1</sup> (NB). NB nucleates bonding inter-phases via complementary 2D- Precursor Phases (2D- PP) instead of thermal activation. 2D-PP relies on Surface Energy Engineering (SEE), which characterizes and then modifies hydroaffinity and surface energy into far-from-equilibrium states. SEE finds that  $\Delta Gs$  for interaction between  $LiNbO_3$  and  $Si/SiO_2$  are both positive and do not favor NB. Hence, SEE on LiNbO<sub>3</sub> and Si/SiO<sub>2</sub> needs to change  $\Delta G$  to negative at RT. Experimental results show that SEE of ?-quartz SiO<sub>2</sub> and LiNbO<sub>3</sub> yield NB at RT.<sup>1</sup> Herbots et al. US Pat. 6613677 (2003), 7,851,365 (2010), 9,018,077 (2015), 9,589,801 (2017), and pending (2020)

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